

QUADRUPLE TRUE/COMPLEMENT BUFFER



The HEF4041B is a quadruple true/complement buffer which provides both an inverted active LOW output ($\bar{O}$) and a non-inverted active HIGH output (O) for each input (I). The buffers exhibit high current output capability suitable for driving TTL or high capacitive loads.

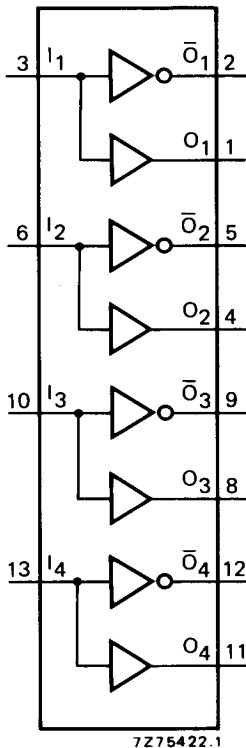


Fig. 1 Functional diagram.

APPLICATION INFORMATION

Some examples of applications for the HEF4041B are:

- LOC MOS to DTL/TTL converter
- High current sink and source driver

FAMILY DATA

I_{DD} LIMITS category BUFFERS

} see Family Specifications

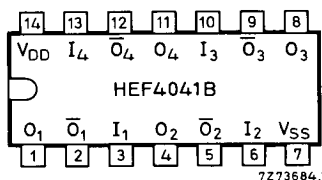


Fig. 2 Pinning diagram.

HEF4041BP : 14-lead DIL; plastic (SOT-27).
HEF4041BD : 14-lead DIL; ceramic (cerdip) (SOT-73).
HEF4041BT : 14-lead mini-pack; plastic (SO-14; SOT-108A).

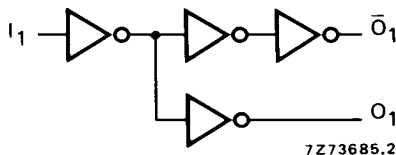


Fig. 3 Logic diagram (one buffer).

D.C. CHARACTERISTICS

 $V_{SS} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD}

	V_{DD} V	V_{OH} V	V_{OL} V	symbol	T_{amb} (°C)				
					-40 min.	+25 typ.	+85 min.	+85 max.	
Output (source) current HIGH	5	4,6		$-I_{OH}$	1,6	1,3	2,6	1,0	mA
	10	9,5			4,5	3,6	7,0	2,7	mA
	15	13,5			16,0	14,0	30,0	10,0	mA
Output (sink) current LOW	5	2,5		I_{OL}	5,0	4,0	8,0	3,0	mA
	4,75		0,4		2,0	1,7	4,0	1,35	mA
	10		0,5		7,5	6,0	12,0	4,5	mA
	15		1,5		23,0	20,0	35,0	15,0	mA

A.C. CHARACTERISTICS

 $V_{SS} = 0\text{ V}$; $T_{amb} = 25\text{ °C}$; $C_L = 50\text{ pF}$; input transition times $\leq 20\text{ ns}$

	V _{DD} V	symbol	min.	typ.	max.	typical extrapolation formula	
Propagation delays							
I _n → O _n	5	t _{PHL}		30	65	ns	17 ns + (0,27 ns/pF) C _L
HIGH to LOW	10			20	40	ns	14 ns + (0,11 ns/pF) C _L
	15			15	30	ns	12 ns + (0,08 ns/pF) C _L
LOW to HIGH	5	t _{PLH}		30	55	ns	17 ns + (0,27 ns/pF) C _L
	10			15	30	ns	9 ns + (0,11 ns/pF) C _L
	15			10	20	ns	7 ns + (0,08 ns/pF) C _L
I _n → $\overline{O}_n$	5	t _{PHL}		35	75	ns	22 ns + (0,27 ns/pF) C _L
HIGH to LOW	10			20	40	ns	14 ns + (0,11 ns/pF) C _L
	15			15	30	ns	12 ns + (0,08 ns/pF) C _L
LOW to HIGH	5	t _{PLH}		35	75	ns	22 ns + (0,27 ns/pF) C _L
	10			20	40	ns	14 ns + (0,11 ns/pF) C _L
	15			15	30	ns	12 ns + (0,08 ns/pF) C _L
Output transition times	5	t _{THL}		25	50	ns	5 ns + (0,40 ns/pF) C _L
O _n → $\overline{O}_n$	10			12	25	ns	2 ns + (0,21 ns/pF) C _L
HIGH to LOW	15			8	20	ns	1 ns + (0,14 ns/pF) C _L
LOW to HIGH	5	t _{TLH}		25	45	ns	5 ns + (0,40 ns/pF) C _L
	10			12	25	ns	2 ns + (0,21 ns/pF) C _L
	15			8	20	ns	1 ns + (0,14 ns/pF) C _L

	V_{DD} V	typical formula for P (μW)	where f_i = input freq. (MHz) f_o = output freq. (MHz) C_L = load capacitance (pF) $\Sigma(f_o C_L)$ = sum of outputs V_{DD} = supply voltage (V)
Dynamic power dissipation per package (P)	5	$3100 f_i + \Sigma(f_o C_L) \times V_{DD}^2$	
	10	$12700 f_i + \Sigma(f_o C_L) \times V_{DD}^2$	
	15	$33800 f_i + \Sigma(f_o C_L) \times V_{DD}^2$	